



1N914 THRU 1N4454

SILICON EPITAXIAL PLANAR DIODES

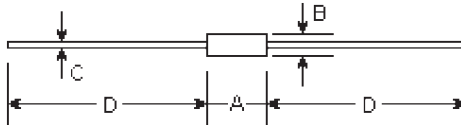
Features

Silicon Epitaxial Planar Diodes
for general purpose and switching

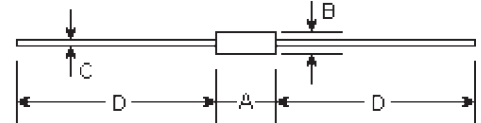
DO-35

The types 1N4149, 1N4447 and 1N4449 are also available in glass case DO-34.

DO-34



DIMENSIONS					
DIM	inches		mm		Note
	Min.	Max.	Min.	Max.	
A	-	0.114	-	2.9	
B	-	0.075	-	1.9	φ
C	-	0.017	-	0.42	φ
D	0.630	-	16.0	-	



DIMENSIONS					
DIM	inches		mm		Note
	Min.	Max.	Min.	Max.	
A	-	0.154	-	3.9	
B	-	0.075	-	1.9	φ
C	-	0.020	-	0.52	φ
D	1.083	-	27.50	-	

Electrical Characteristics

Type	Peak reverse voltage	Max. aver. rectified current	Max. power dissip. at 25°C	Max. junction temperature	Max. forward voltage drop		Max. reverse current		Max. reverse recovery time	
	V_{RM} V	I_O mA	P_{tot} mW	T_J °C	V_F V	at I_F mA	I_R nA	at V_R V	t_{rr} nS	Conditions
1N914	100	75	500	200	1.0	10	25	20	Max. 4.0	$I_F=10$ mA, $V_R=6$ V, $R_L=100\ \Omega$, to $I_R=1$ mA
1N4149 ⁽¹⁾	100	150	500	200	1.0	10	25	20	Max. 4.0	$I_F=10$ mA, $V_R=6$ V, $R_L=100\ \Omega$, to $I_R=1$ mA
1N4150	50	200	500	200	1.0	200	100	50	Max. 4.0	$I_F=I_R=10$ to 200 mA, to 0.1 I_F
1N4152	40	150	400	175	0.55	0.10	50	30	Max. 2.0	$I_F=10$ mA, $V_R=6$ V, $R_L=100\ \Omega$, to $I_R=1$ mA
1N4153	75	150	400	175	0.55	0.10	50	50	Max. 2.0	$I_F=10$ mA, $V_R=6$ V, $R_L=100\ \Omega$, to $I_R=1$ mA
1N4154	35	150 ⁽²⁾	500	200	1.0	0.10	100	25	Max. 2.0	$I_F=10$ mA, $V_R=6$ V, $R_L=100\ \Omega$, to $I_R=1$ mA
1N4447 ⁽¹⁾	100	150	500	200	1.0	20	25	20	Max. 4.0	$I_F=10$ mA, $V_R=6$ V, $R_L=100\ \Omega$, to $I_R=1$ mA
1N4449 ⁽¹⁾	100	150	500	200	1.0	30	25	20	Max. 4.0	$I_F=10$ mA, $V_R=6$ V, $R_L=100\ \Omega$, to $I_R=1$ mA
1N4450	40	150	400	175	0.54	0.50	50	30	Max. 4.0	$I_F=I_R=10$ mA, to $I_R=1$ mA
1N4451	40	150	400	175	0.50	0.10	50	30	Max. 10	$I_F=I_R=10$ mA, to $I_R=1$ mA
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1.0	10	100	50	Max. 4.0	$I_F=I_R=10$ mA, to $I_R=1$ mA

Notes:

(1) These diodes are also available in glass case DO-34

(2) Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature

Parameters for diodes in case DO-34:

$P_{tot}=300$ mW

$T_S=-65$ to $+175^\circ\text{C}$

$T_J=175^\circ\text{C}$

$R_{\theta JA} \leq 0.4$ K/mW